

TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

# GT5G131

## Strobe Flash Applications

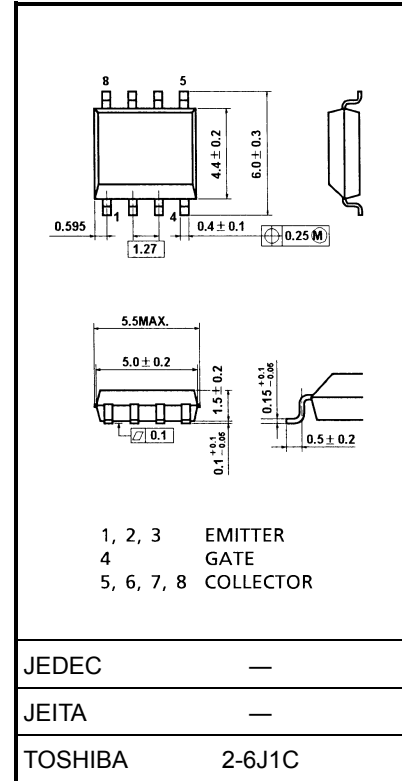
- 3-V gate drive voltage:  $V_{GE} = 3.0 \text{ V (min)}$  (@ $I_C = 130 \text{ A}$ )
- Supplied in compact and thin package requires only a small mounting area
- 5th generation (trench gate structure) IGBT
- Enhancement-mode
- Peak collector current:  $I_C = 130 \text{ A (max)}$

## Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

| Characteristics                      | Symbol    | Rating    | Unit             |
|--------------------------------------|-----------|-----------|------------------|
| Collector-emitter voltage            | $V_{CES}$ | 400       | V                |
| Gate-emitter voltage                 | DC        | $V_{GES}$ | $\pm 6$          |
|                                      | Pulse     | $V_{GES}$ | $\pm 8$          |
| Collector current                    | DC        | $I_C$     | 5                |
|                                      | 1 ms      | $I_{CP}$  | 130              |
| Collector power dissipation (Note 1) | $P_C$     | 1.1       | W                |
| Junction temperature                 | $T_j$     | 150       | $^\circ\text{C}$ |
| Storage temperature range            | $T_{stg}$ | -55~150   | $^\circ\text{C}$ |

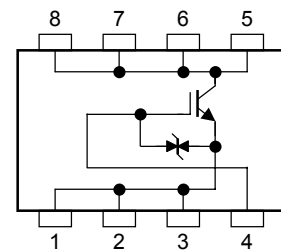
Note 1: Drive operation: Mount on glass epoxy board [ $1 \text{ inch}^2 \times 1.5 \text{ t}$ ]

Unit: mm



Weight: 0.080 g (typ.)

## Equivalent Circuit



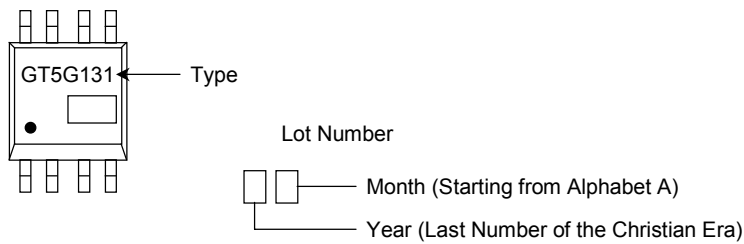
These devices are MOS type. Users should follow proper ESD handling procedures. Operating condition of turn-off  $dv/dt$  should be lower than  $400 \text{ V}/\mu\text{s}$ .

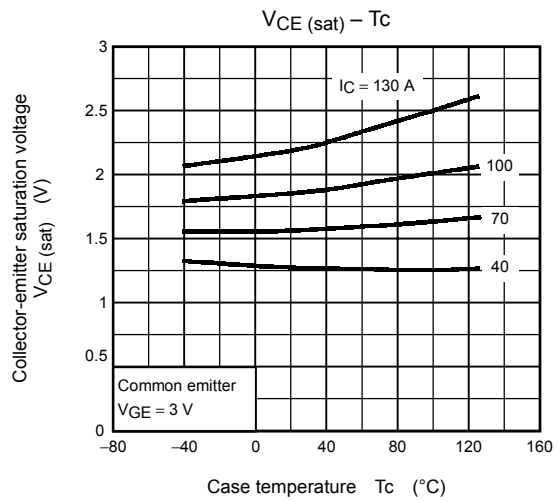
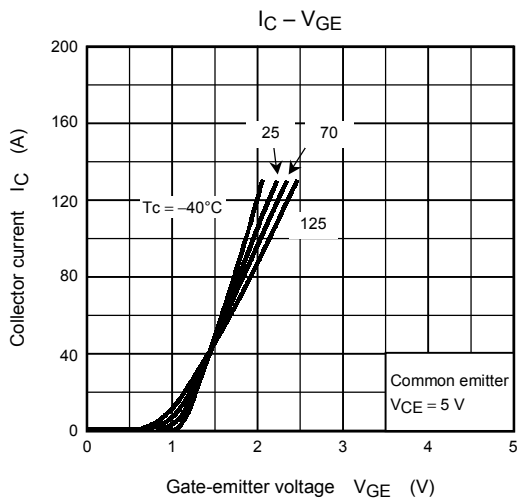
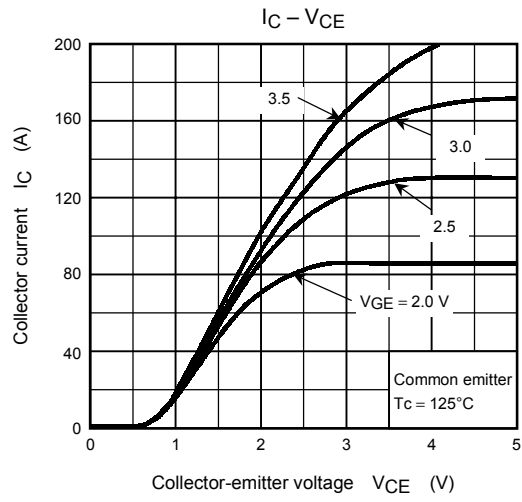
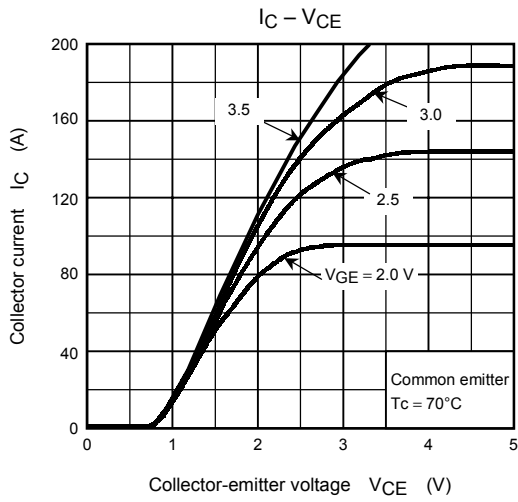
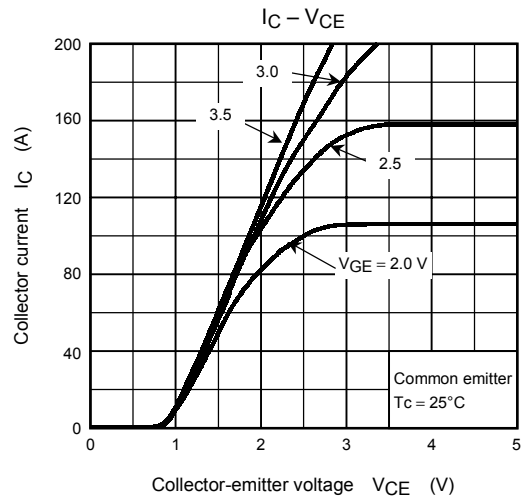
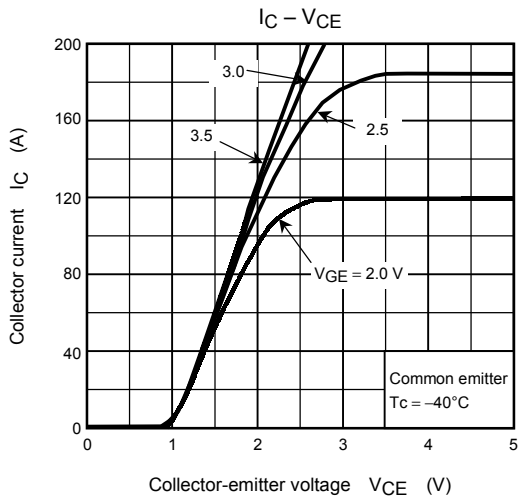
## Electrical Characteristics (Ta = 25°C)

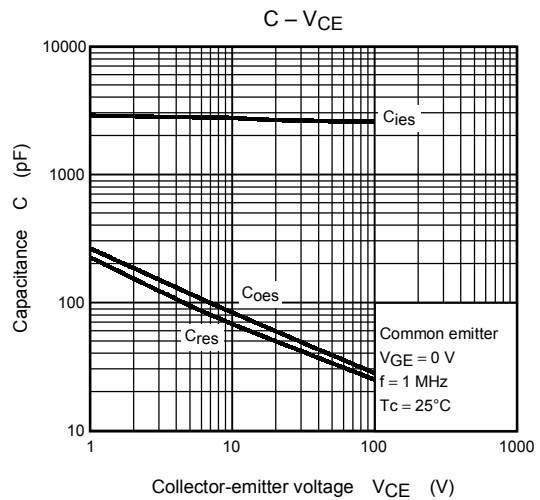
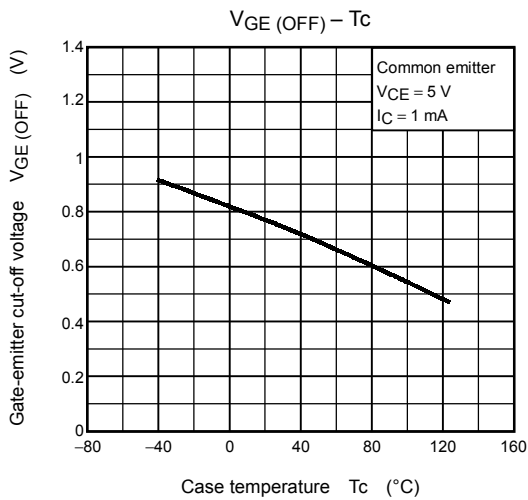
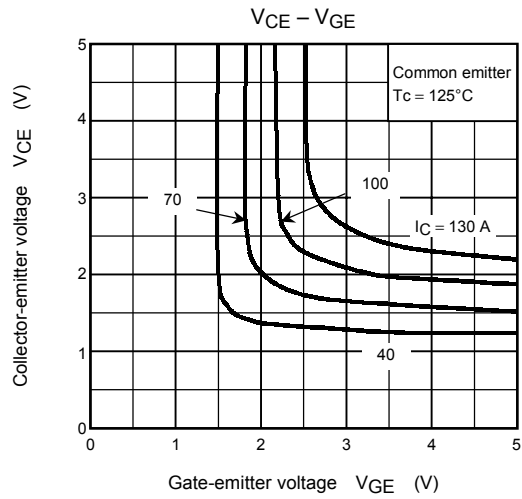
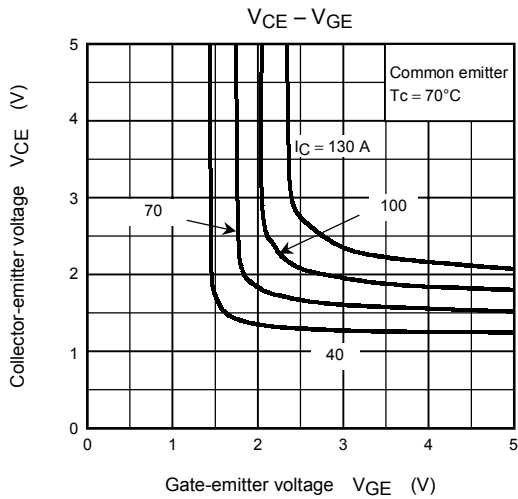
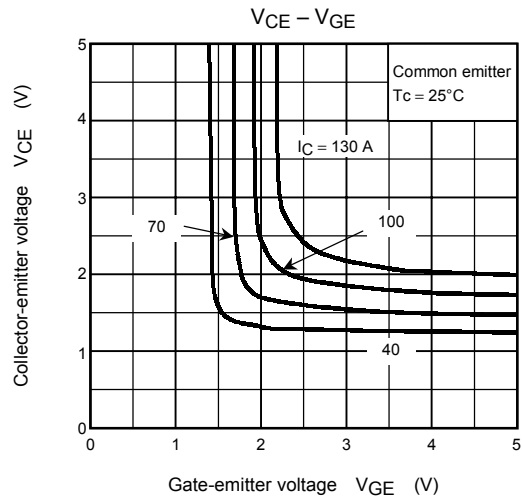
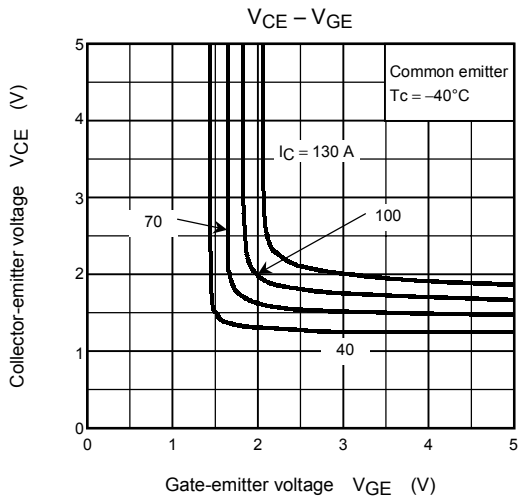
| Characteristics                      |               | Symbol               | Test Condition  | Min | Typ. | Max      | Unit                 |
|--------------------------------------|---------------|----------------------|---|-----|------|----------|----------------------|
| Gate leakage current                 |               | $I_{GES}$            | $V_{GE} = \pm 6\text{ V}, V_{CE} = 0$   | —   | —    | $\pm 10$ | $\mu\text{A}$        |
| Collector cut-off current            |               | $I_{CES}$            | $V_{CE} = 400\text{ V}, V_{GE} = 0$   | —   | —    | 10       | $\mu\text{A}$        |
| Gate-emitter cut-off voltage         |               | $V_{GE(\text{OFF})}$ | $I_C = 1\text{ mA}, V_{CE} = 5\text{ V}$  | 0.5 | —    | 1.0      | V                    |
| Collector-emitter saturation voltage |               | $V_{CE(\text{sat})}$ | $I_C = 130\text{ A}, V_{GE} = 3\text{ V}$   | —   | 2.2  | 7.0      | V                    |
| Input capacitance                    |               | $C_{ies}$            | $V_{CE} = 10\text{ V}, V_{GE} = 0, f = 1\text{ MHz}$  | —   | 2800 | —        | pF                   |
| Switching time                       | Rise time     | $t_r$                | <p> <math>V_{IN}: t_r \leq 100\text{ ns}</math><br/> <math>t_f \leq 100\text{ ns}</math><br/>                     Duty cycle <math>\leq 1\%</math> </p> | —   | 1.3  | —        | $\mu\text{s}$        |
|                                      | Turn-on time  | $t_{on}$             |   | —   | 1.4  | —        |                      |
|                                      | Fall time     | $t_f$                |   | —   | 1.5  | —        |                      |
|                                      | Turn-off time | $t_{off}$            |   | —   | 1.8  | —        |                      |
| Thermal resistance (Note 2)          |               | $R_{th(j-a)}$        | —   | —   | —    | 114      | $^{\circ}\text{C/W}$ |

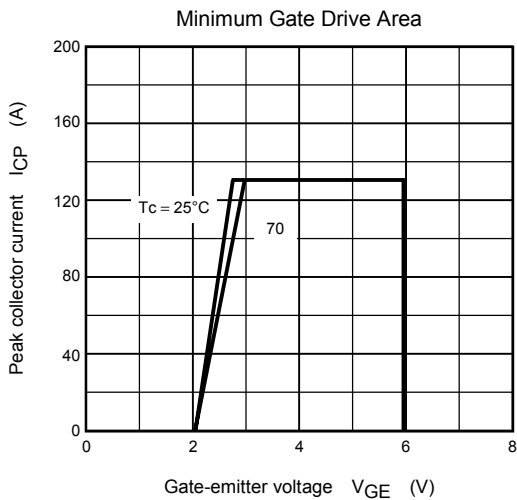
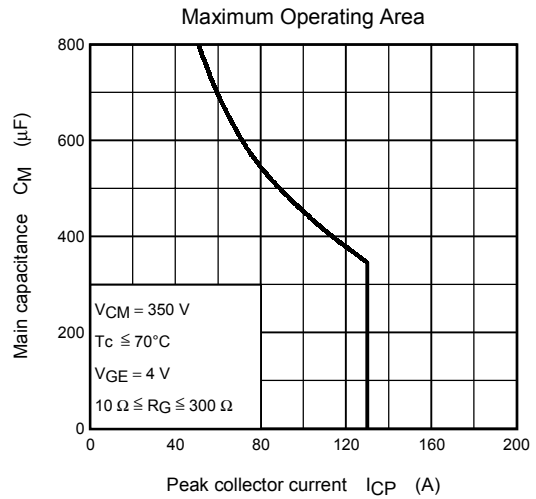
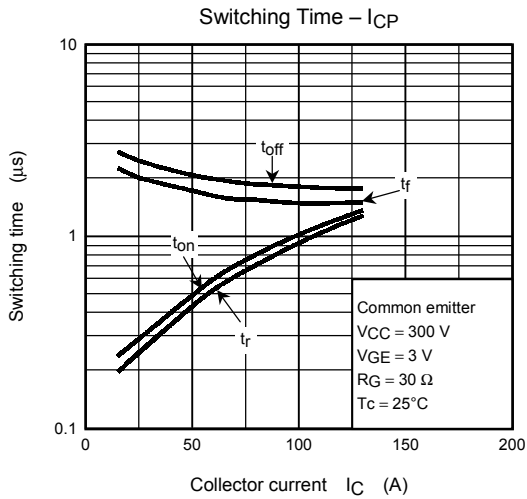
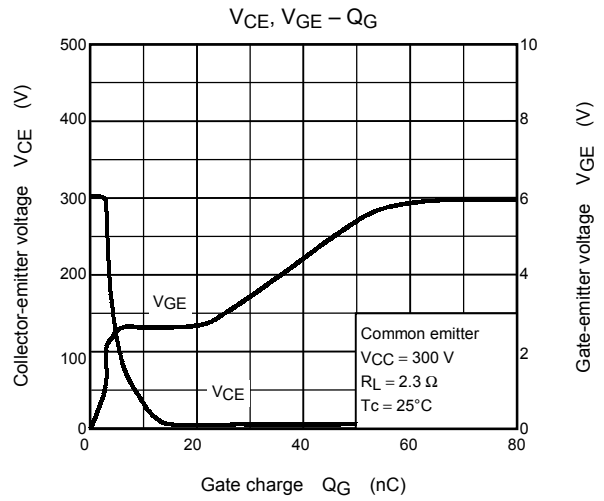
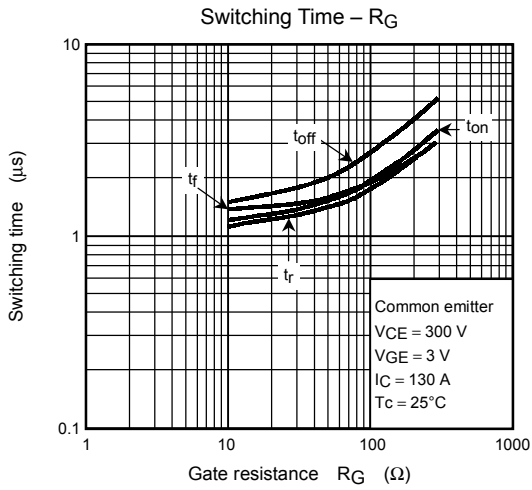
Note 2: Drive operation: Mount on glass epoxy board [1 inch<sup>2</sup> × 1.5 t]

## Marking









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